

900V, 50A, N-channel SiC power MOSFET
General Description:

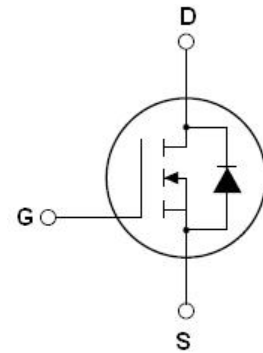
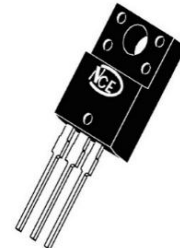
NCES090P050F is a SiC MOSFET that contributes to miniaturization and low power consumption of applications. This product achieves industry-leading low on-resistance without sacrificing short-circuit withstand time.

Features

- Low on-resistance
- Fast switching speed
- Fast reverse recovery
- Easy to parallel
- Simple to drive
- Pb-free lead plating ; RoHS compliant

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives


Schematic diagram

TO-220F-3L
Package Marking and Ordering Information

Device	Device Package	Device Marking
NCES090P050F	TO-220F-3L	NCES090P050F

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	900	V
Gate-Source Voltage,max static voltage	V _{GS}	-10 to +24	V
Gate-Source Voltage,max transient voltage (Note 1)	V _{GS}	-11 to +26	V
Drain Current-Continuous (Note 2)	I _D	50	A
Drain Current-Continuous(T _c =100°C)	I _D (100°C)	35	A
Pulsed Drain Current (Note 3)	I _{DM}	125	A
Maximum Power Dissipation	P _D	T _{vj} = 25°C	36
		T _{vj} = 100°C	18
Recommended turn-on gate - source drive voltage	V _{GS_on}	+15 to +18	V
Recommended turn-off gate - source drive voltage	V _{GS_off}	-4 to 0	V
Virtual junction temperature	T _{vj}	175	°C
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction to case	4.2	°C/W
R _{θJA}	Thermal Resistance, Junction to ambient	62	°C/W

Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =100μA	900			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =900V, V _{GS} =0V	T _{vj} = 25°C	1	80	μA	
			T _{vj} = 175°C	2			
Gate-Body Leakage Current	I _{GSS}	V _{GS} =-10V / +22V, V _{DS} =0V			±100	nA	
On Characteristics (Note 4)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =6mA	T _{vj} = 25°C	1.9	3.0	4.8	V
			T _{vj} = 175°C		2.1		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =18V, I _D =20A	T _{vj} = 25°C		50	65	mΩ
			T _{vj} = 175°C		58		
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =15V, I _D =20A	T _{vj} = 25°C		63	82	mΩ
			T _{vj} = 175°C		74		
Gate input resistance	R _G	f=1MHZ, open drain		2.5		Ω	
Forward Transconductance	g _{FS}	V _{DS} =20V, I _D =20A		12.5		S	
Dynamic Characteristics (Note 5)							
Input Capacitance	C _{ISS}	V _{DS} =500V, V _{GS} =0V, f=1MHz		1680		pF	
Output Capacitance	C _{OSS}			112		pF	
Reverse Transfer Capacitance	C _{rss}			4.7		pF	
C _{OSS} stored energy	E _{OSS}			22.3		μJ	
Output charge	Q _{OSS}	Calculated by C _{OSS} (f)V _{DS} @1MHz		120		nC	
Effective output capacitance, energy related	C _{O(er)}	V _{DS} =0-500V, V _{GS} =0V		178		pF	
Effective output capacitance, time related	C _{O(tr)}	I _C =constant, V _{DS} =0-500V, V _{GS} =0V		240		pF	
Switching Characteristics (Note 5)							
Turn-on Delay Time	t _{d(on)}	V _{DD} =500V, I _D =20A, V _{GS} =+18V / -3V, R _G =2.7Ω, L=200μH		11.3		ns	
Turn-on Rise Time	t _r			16.5		ns	
Turn-Off Delay Time	t _{d(off)}			26.2		ns	
Turn-Off Fall Time	t _f			8.2		ns	
Turn-on energy	E _{on}	V _{DD} =500V, I _D =20A, V _{GS} =+18V / -3V, R _G =2.7Ω, L=200μH	T _{vj} = 25°C		90	μJ	
			T _{vj} = 175°C		95	μJ	
Turn-off energy	E _{off}		T _{vj} = 25°C		31	μJ	
			T _{vj} = 175°C		35	μJ	
Total Gate Charge	Q _g	V _{DS} =500V, I _D =20A, V _{GS} =-3/18V		64		nC	
Gate-Source Charge	Q _{gs}			18		nC	
Gate-Drain Charge	Q _{gd}			17		nC	

Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 4)	V _{SD}	V _{GS} =0V, I _{SD} =20A	T _{vj} = 25°C		3.4	V
			T _{vj} = 175°C		3.0	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =20A, V _R =500V, di/dt = 2830A/μs (Note3)		16.2		ns
Reverse Recovery Charge	Q _{rr}			248		nC
Peak reverse recovery current	I _{rrm}			30.1		A

Notes:

- t_p < 500ns, D < 0.01
- TO220 equivalent. Limited by T_j max.
- PW ≤ 10μs, Duty cycle ≤ 1%
- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production

Test Circuit

Fig.1-1 Gate Charge Measurement Circuit



Fig.1-2 Gate Charge Waveform

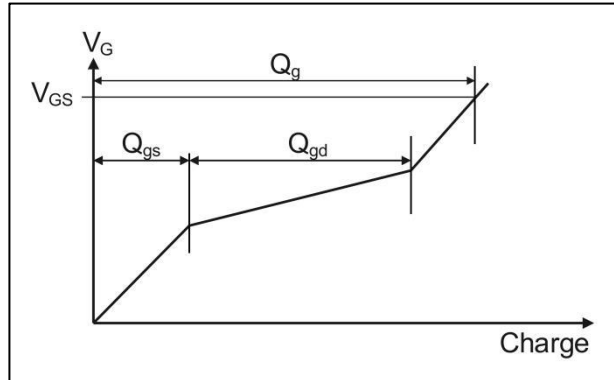


Fig.2-1 Switching Characteristics Measurement Circuit

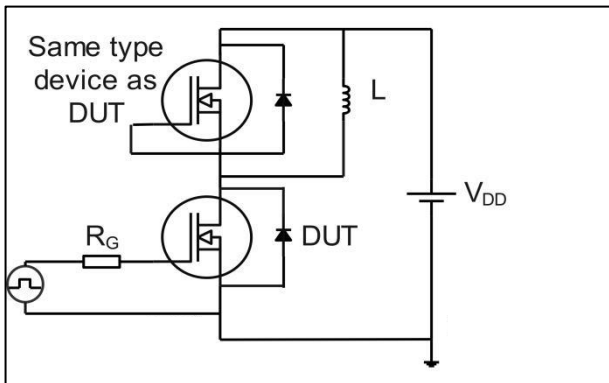
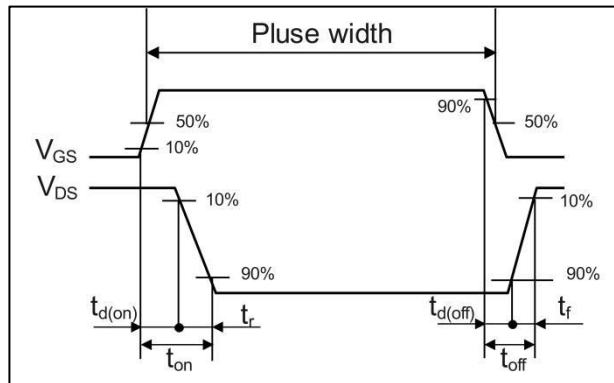


Fig.2-2 Waveforms for Switching Time



Typical Electrical and Thermal Characteristics

Fig.1 Power Dissipation Derating Curve

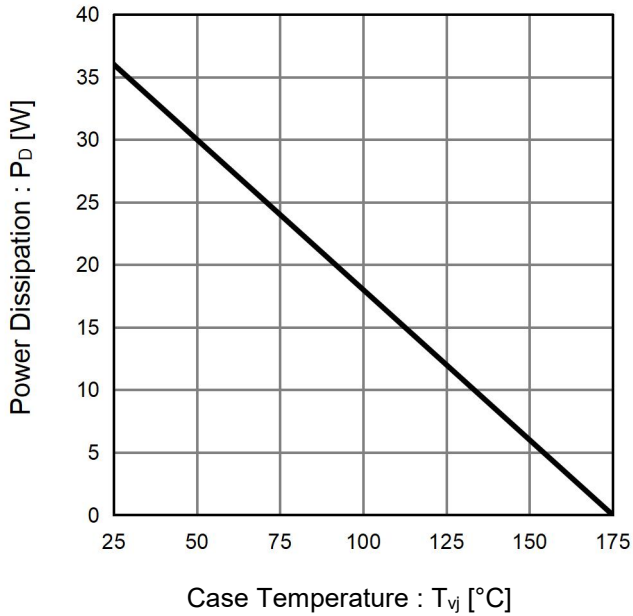


Fig.2 Maximum Safe Operating Area

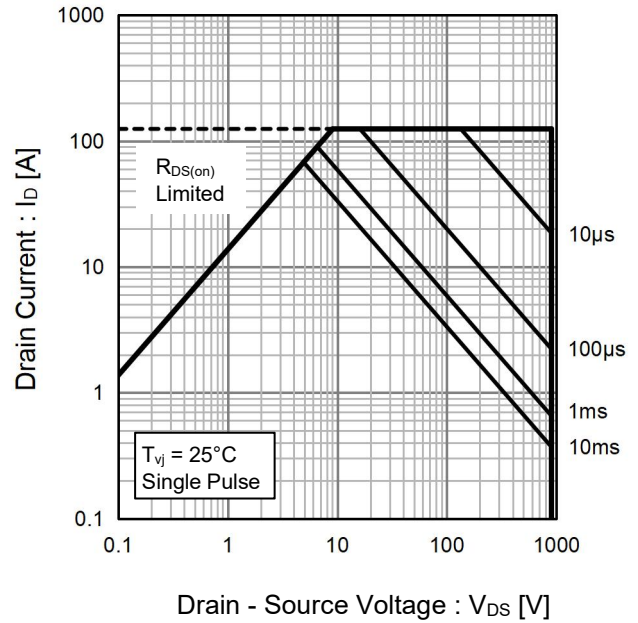


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width

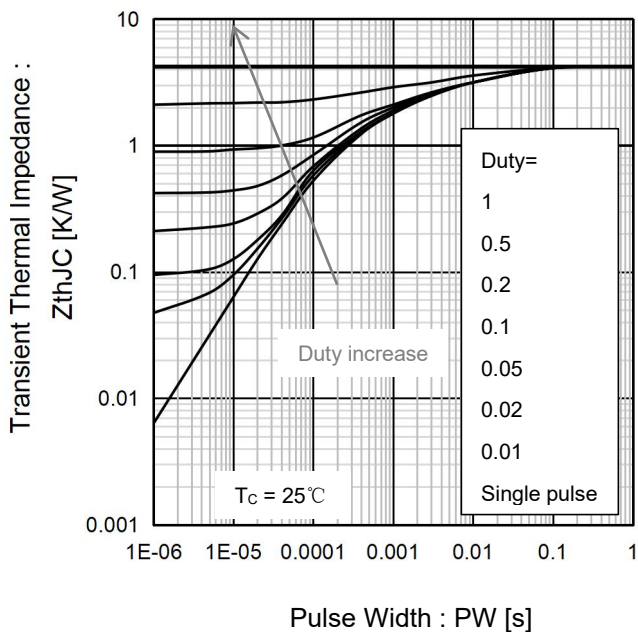


Fig.4 $T_{vj} = 25^{\circ}\text{C}$ Typical Output Characteristics

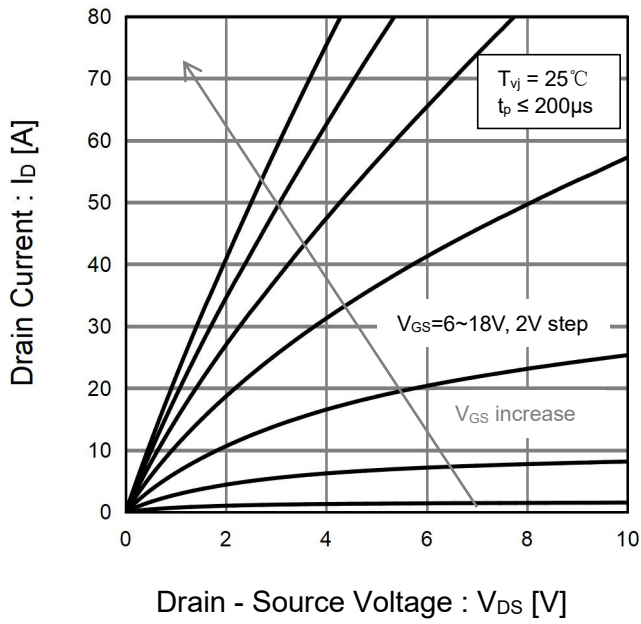


Fig.5 $T_{vj} = 25^{\circ}\text{C}$ 3rd Quadrant Characteristics

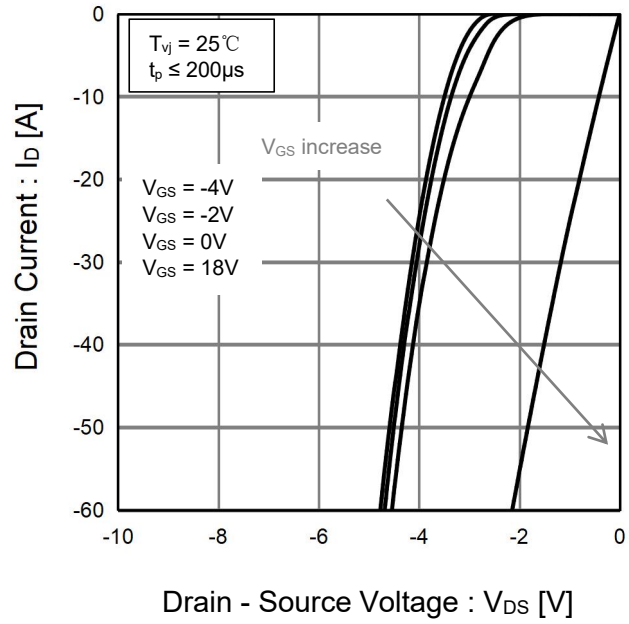


Fig.6 $T_{vj} = 175^{\circ}\text{C}$ Typical Output Characteristics

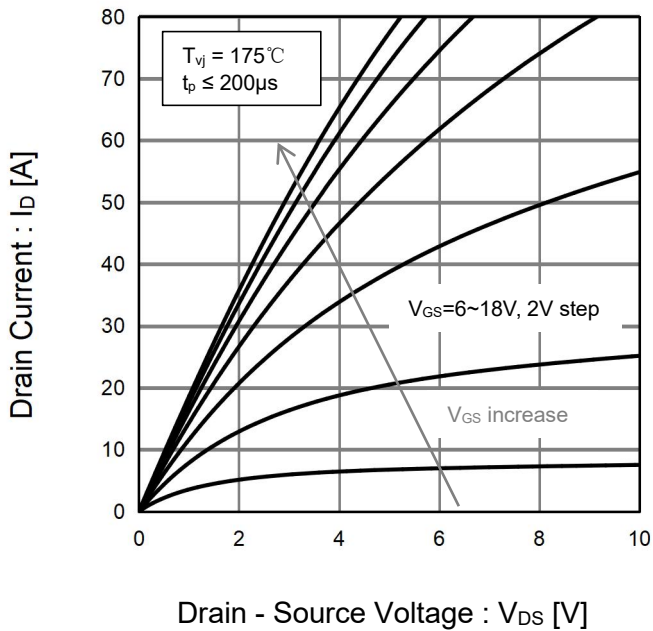


Fig.7 $T_{vj} = 175^{\circ}\text{C}$ 3rd Quadrant Characteristics

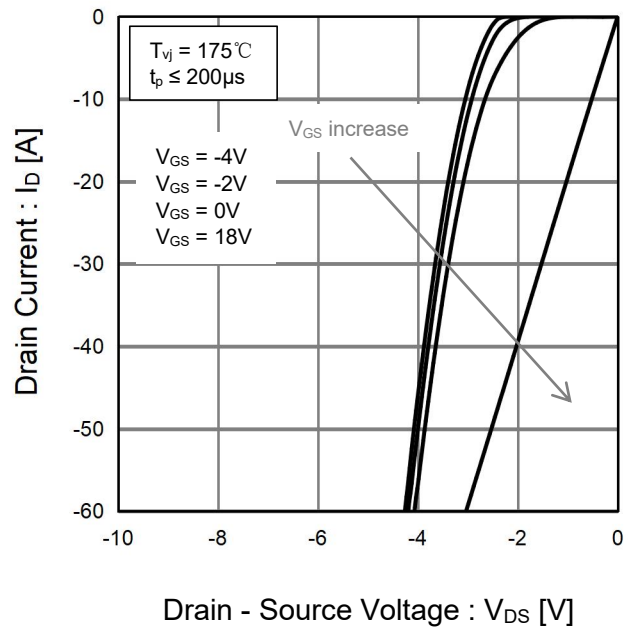


Fig.8 Typical Transfer Characteristics

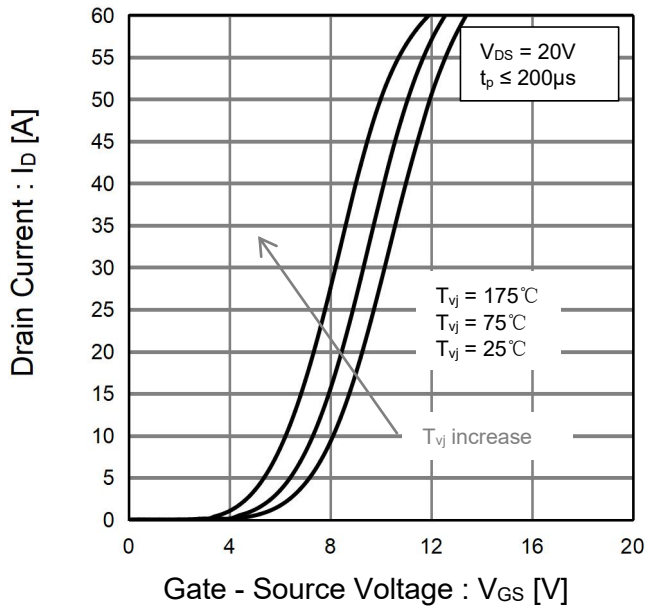


Fig.9 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

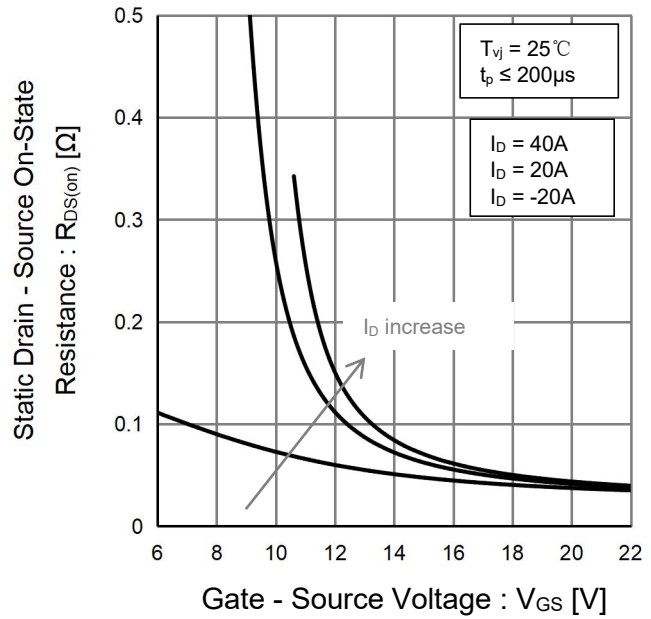


Fig.10 Static Drain - Source On - State Resistance vs. Drain Current

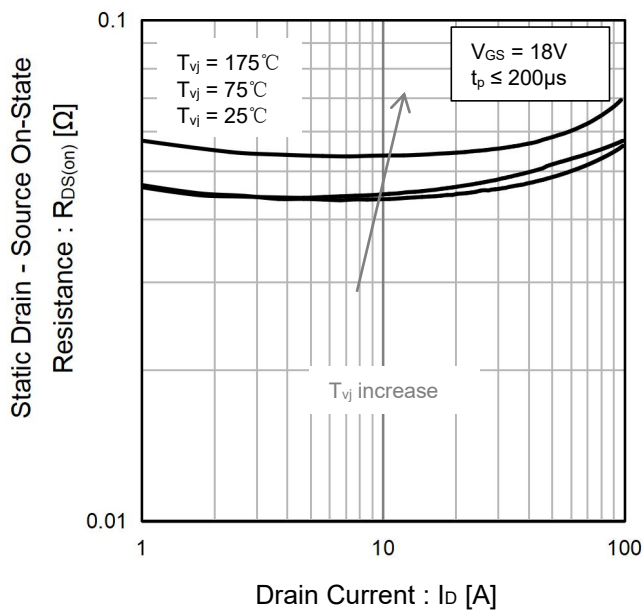


Fig.11 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

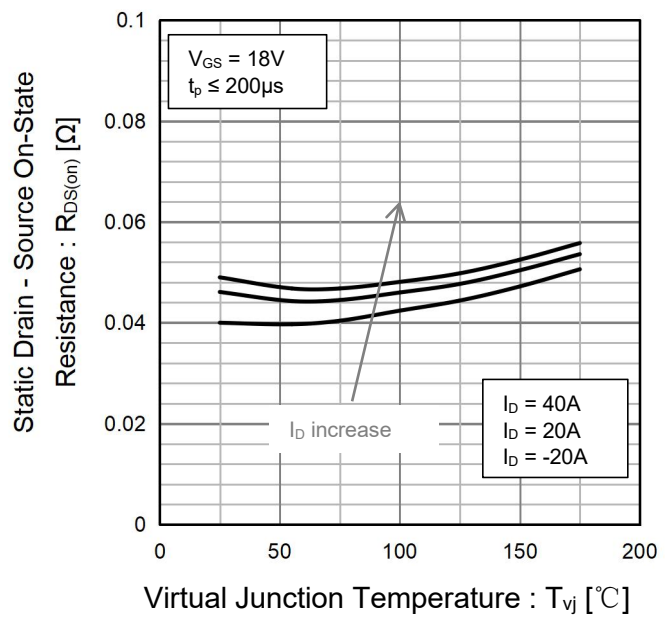


Fig.12 Body Diode Forward Voltage vs. Gate - Source Voltage

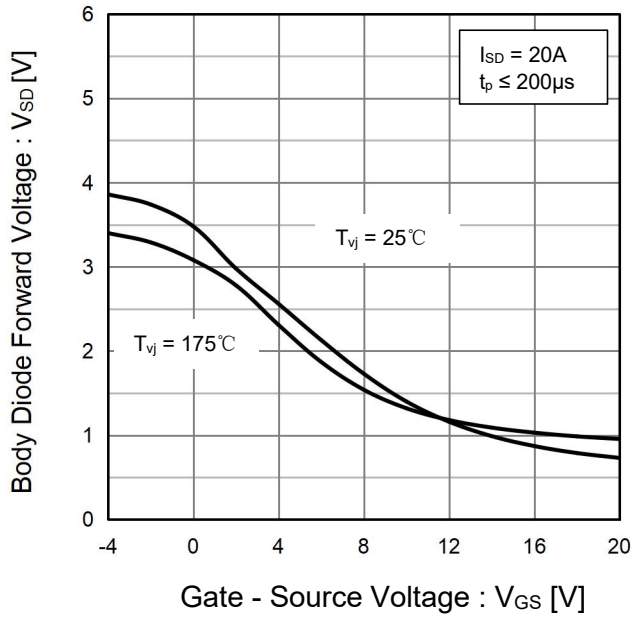


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

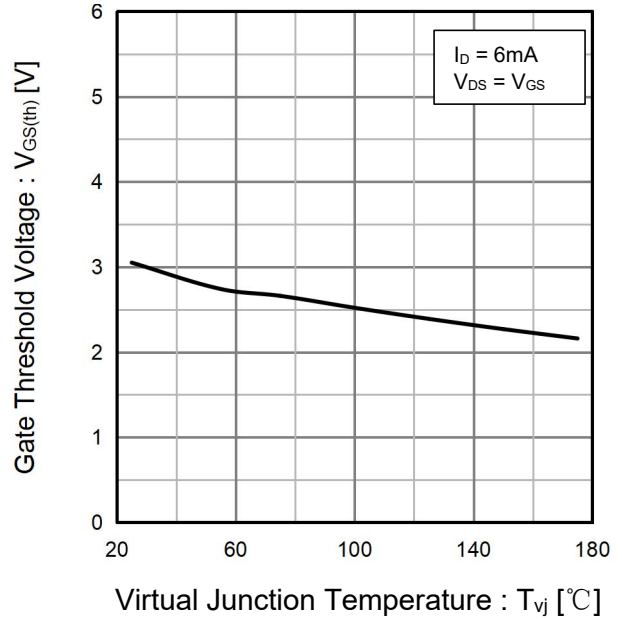


Fig.14 Typical Capacitance vs. Drain - Source Voltage

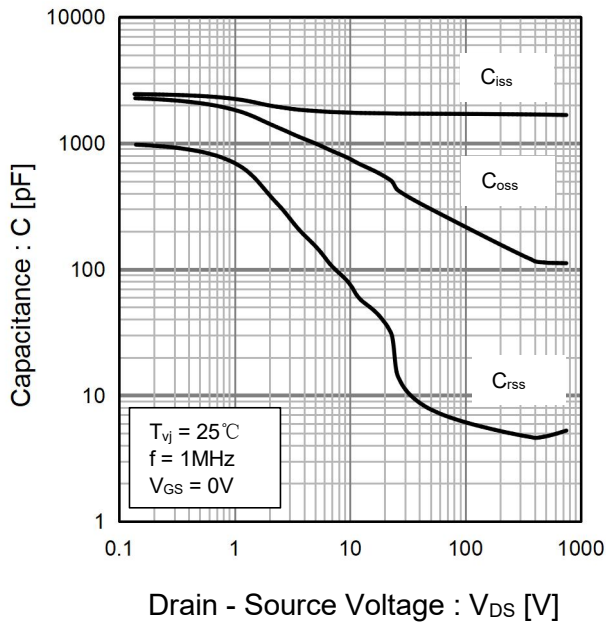


Fig.15 Coss Stored Energy

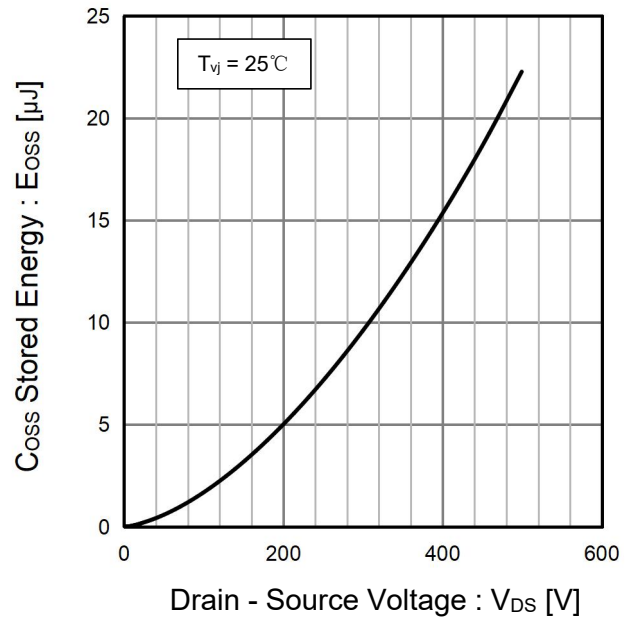


Fig.16 Dynamic Input Characteristics

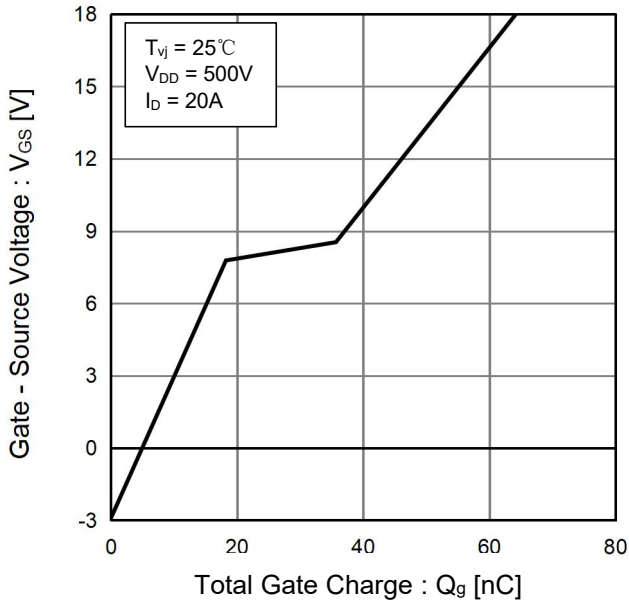


Fig.17 Typical Switching Time vs. External Gate Resistance

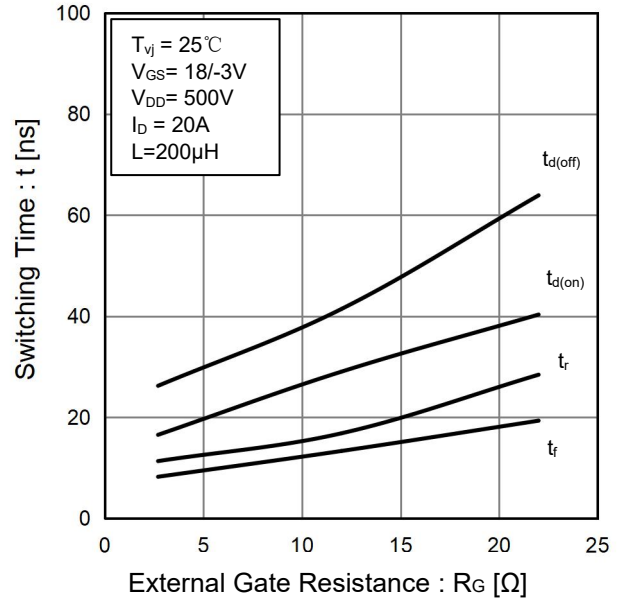


Fig.18 Typical Switching Energy vs. External Gate Resistance

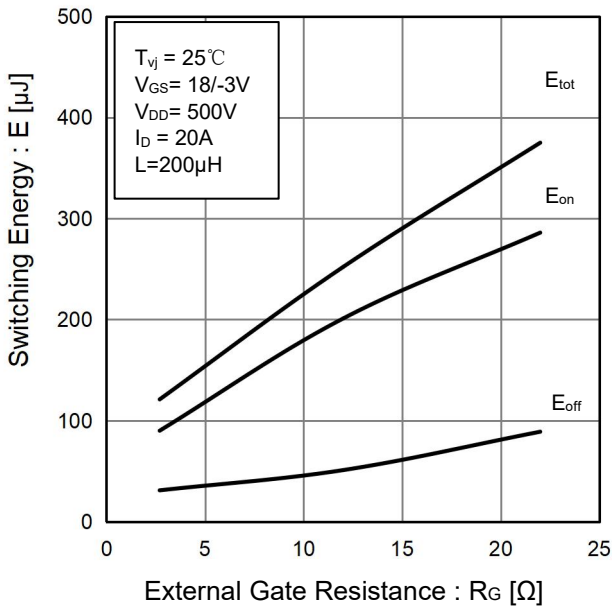


Fig.19 Typical Switching Energy vs. Drain Current

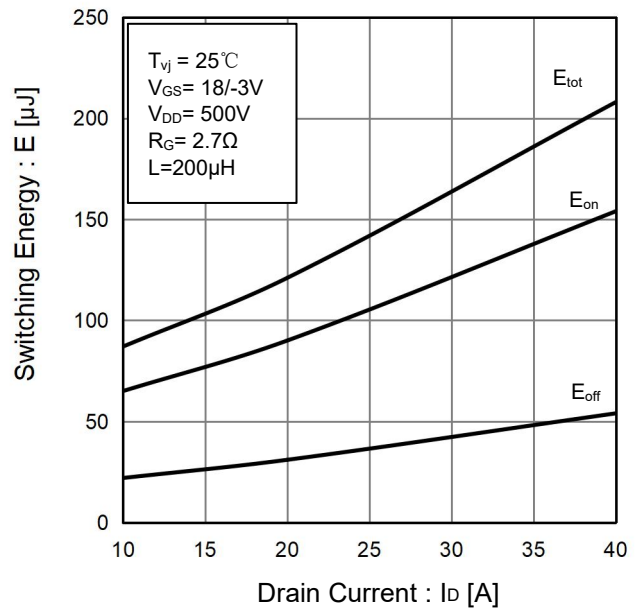
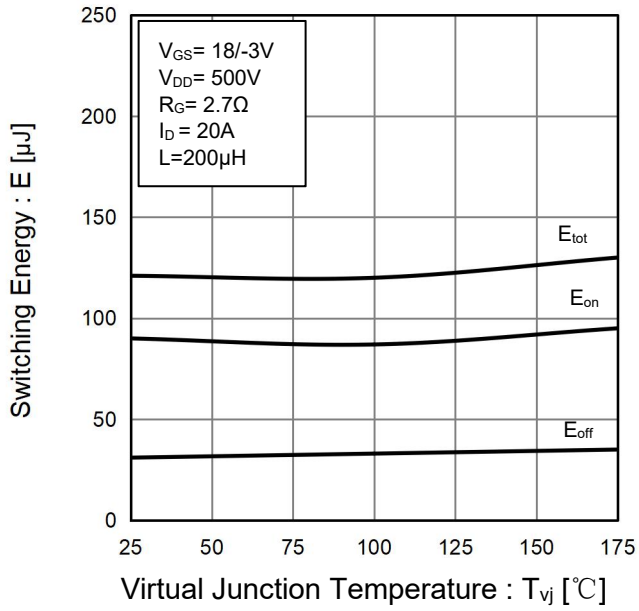
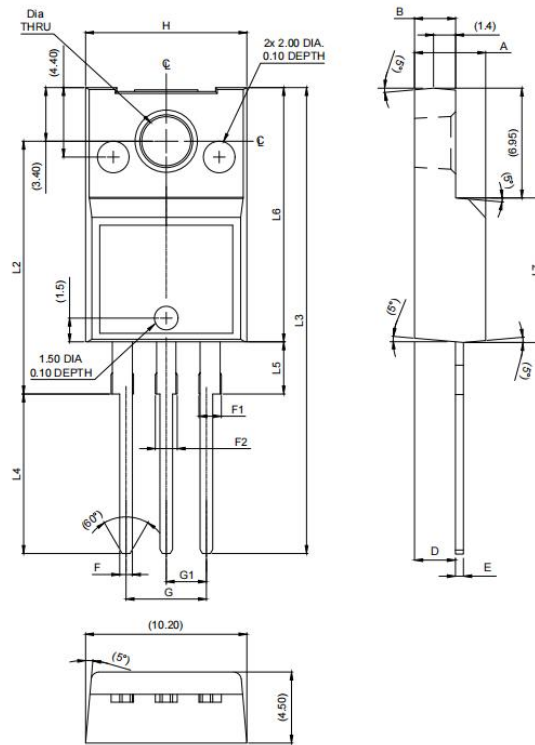


Fig.20 Typical Switching Energy vs. Virtual Junction Temperature



TO-220F-3L-B Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
B	2.50	2.70	0.098	0.106
D	2.50	2.75	0.098	0.108
E	0.45	0.70	0.018	0.028
F	0.75	1.00	0.029	0.039
F1	1.15	1.50	0.045	0.059
F2	1.15	1.50	0.045	0.059
G	4.95	5.20	0.19	0.20
G1	2.40	2.70	0.09	0.11
H	10.00	10.40	0.39	0.41
L2	16.00		0.63	
L3	28.60	30.60	1.12	1.20
L4	9.80	10.60	0.39	0.42
L5	2.90	3.60	0.11	0.14
L6	15.90	16.40	0.62	0.64
L7	9.00	9.30	0.35	0.37
Dia	3.00	3.20	0.12	0.13

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